

Remarks

The amendment to the specification updates the data regarding the parent application. Applicants submit that the amendment does not add any new matter to the disclosure.

Applicants attorney hereby certifies that attached declaration under 37 CFR 1.131 of the inventors is a true copy of the declaration submitted in the parent application. Applicants submit that the Dammel et al. reference is not prior art against the claimed invention in view of the declaration of the inventors under 37 CFR 1.131.

Specifically, the declaration and attached exhibits 1-6 show that prior to May 11, 2001, the present inventors conceived and reduced to practice of the invention for forming a patterned material structure on a substrate, said material being selected from the group consisting of semiconductors, ceramics and metals, the method comprising: (A) providing a substrate with a layer of the material, (B) applying a resist composition to the substrate to form a resist layer on the substrate, the resist composition comprising (a) an imaging polymer, and (b) a radiation sensitive acid generator, the imaging polymer comprising cyano-modified acrylic monomer units comprising an acrylic moiety with a cyano group pendant therefrom; (C) patternwise exposing the substrate to radiation whereby acid is generated by the acid generator in exposed regions of the resist layer by the radiation, (D) contacting the substrate with an aqueous alkaline developer solution, whereby the exposed regions of the resist layer are selectively dissolved by the developer solution to reveal a patterned resist structure, and (E) transferring resist structure pattern to the material layer, by etching into the material layer through spaces in the resist structure pattern. In exhibits 1-3, the benefits of using polymers containing cyano-modified acrylic

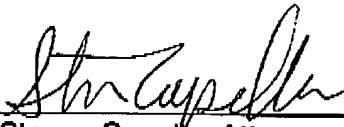
monomers are disclosed on page 2, under items 1 and 2 of the main idea section. The benefits include etch resistance, a property associated with the pattern transfer step (E). Exhibit 4 shows laboratory notebook entries prior to May 11, 2001 documenting synthesis of resist polymers WJL-1 through WJL-5 containing cyano-modified acrylic monomer units comprising an acrylic moiety with a cyano group pendant therefrom. Exhibit 5 shows formulation sheet dated prior to May 11, 2001 for resist F801 containing polymer WJL-1 of Exhibit 4. Exhibit 6 shows formulation log printout indicating exposure of resist composition F801 prior to May 11, 2001. Applicants submit that the pattern transfer step is obvious from the indicated utility of the compositions of the invention as photoresist. Thus, applicants submit that the declaration establishes conception and reduction to practice of the invention of the independent claim in the application prior to May 11, 2001.

Applicants submit that the evidence is sufficient to persuade one skilled in the art that applicants were in possession of the invention as claimed.

For the above reasons, applicants submit that the claims are patentable over the prior art of record and that the application is in condition for allowance. Such allowance is earnestly and respectfully solicited.

Respectfully submitted,

Wenjie Li et al.

By 
Steven Capella, Attorney
Reg. No. 33,086
Telephone: 845-894-3669